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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/680,229	10/08/2003	Kui Yao	4249-0112P	5826
	7590 10/10/200 ART KOLASCH & BI	EXAMINER		
PO BOX 747	CH VA 22040 0747	TALBOT, BRIAN K		
FALLS CHURCH, VA 22040-0747			ART UNIT	PAPER NUMBER
			1792	
			NOTIFICATION DATE	DELIVERY MODE
			10/10/2008	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

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	Application No.	Applicant(s)		
	10/680,229	YAO ET AL.		
Office Action Summary	Examiner	Art Unit		
	Brian K. Talbot	1792		
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	correspondence address		
A SHORTENED STATUTORY PERIOD FOR REPL WHICHEVER IS LONGER, FROM THE MAILING D - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailin earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tin will apply and will expire SIX (6) MONTHS from e, cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).		
Status				
1) Responsive to communication(s) filed on 7/29	s action is non-final. nce except for formal matters, pro			
Disposition of Claims				
4)	wn from consideration. is/are rejected.			
Application Papers				
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) accomposed applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Example 11.	cepted or b) objected to by the liderawing(s) be held in abeyance. See tion is required if the drawing(s) is objected.	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).		
Priority under 35 U.S.C. § 119				
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 				
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal F 6) Other:	ate		

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Continued Examination Under 37 CFR 1.114

- 1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 7/29/08 has been entered.
- 2. Claims 5-11,15,18,20,23 and 35-38 have been canceled. Clams 1-4,12-14,16,17,19,21,22 and 24-34 remain in the application.
- 3. The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.

Claim Rejections - 35 USC § 103

4. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later

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invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

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5. Claims 1-4,12-14,16,17,19,21,24-26,28-31,33 and 34 are rejected under 35 U.S.C. 103(a) as being unpatentable over GB 2161647 in combination with Buchanan et al. (4,283,228) further in combination with Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" still further in combination with Srivastava et al. (5,433,917).

GB 2161647 teaches a piezoelectric device whereby a piezoelectric layer is formed from a composition including piezoelectric powder and a glass–like binding agent. The piezoelectric material is PZT while the binding agent is lead borosilicate. A liquid carrier is utilized to form a paste for screen printing the piezoelectric material to form a film (abstract). After screen printing, the piezoelectric layer is fired by heating to form the layer. The thickness can be from 10-100 microns. The grain size of the powder is 5-10 microns or less. The liquid carrier is ethyl cellulose and terpineol. Electrodes can be applied by a printing process to the PZT film and include silver (pg. 1, line 95 – pg. 4, line 20).

GB 2161647 fails to teach the liquid phase precursor of metal oxide for the binding agent.

Buchanan et al. (4,283,228) teaches low temperature densification of PZT ceramics. The addition of 1-6 weight percent of V_2O_5 promotes rapid densification and therefore lower temperatures of sintering PZT (abstract). The V_2O_5 can be added as a salt or added with an alcohol and a dispersant (col. 2, lines 5-15 and col. 4, lines 25-35). The V_2O_5 can be used a s a sintering aid.

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Therefore it would have been obvious for one skilled in the art at the time the invention was made to have modified GB 2161647 PZT process by incorporating the "binding agent" in liquid form as evidenced by Buchanan et al. (4,283,228) with the expectation of achieving similar success.

GB 2161647 in combination with Buchanan et al. (4,283,228) fail to teach milling the PZT powder and carrier to form a paste.

Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" teaches PZT films by taking ceramic powders and organic carrier (terpeinol and ethyl cellulose) and milling to form a paste to be screen printed (pg. 5400, col. 2).

Therefore it would have been obvious for one skilled in the art at the time the invention was made to have modified GB 2161647 in combination with Buchanan et al. (4,283,228) PZT process by incorporating a milling step to form the paste as evidenced by Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" with the expectation of achieving similar success.

GB 2161647 in combination with Buchanan et al. (4,283,228) further in combination with Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" fails to teach the "binding agent" being in liquid phase and comprising LiO₂ and B₂O₃ and combination thereof.

Srivastava et al. (5,433,917) teaches PZT ceramic compositions having reduced sintering temperatures and process for producing the same. Srivastava et al. (5,433,917) teaches liquid phase sintering agents including metal oxides of Li and Bi (col. 2, lines 6-15).

Therefore it would have been obvious at the time the invention was made to have modified GB 2161647 in combination with Buchanan et al. (4,283,228) further in combination with Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" process by utilizing liquid phase sintering aids for PZT formation including LiO₂ and B₂O₃ and combination thereof as evidenced by Srivastava et al. (5,433,917) with the expectation of achieving similar success and utilizing the advantages associated therewith such as its melting temperature which enhances low temperature sintering.

Claim 22 is rejected under 35 U.S.C. 103(a) as being unpatentable over GB 2161647 in combination with Buchanan et al. (4,283,228) further in combination with Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" still further in combination with Srivastava et al. (5,433,917) further in combination with Maas et al. "Thickfilm printing of PZT onto silicon".

GB 2161647 in combination with Buchanan et al. (4,283,228) further in combination with Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" still further in combination with Srivastava et al. (5,433,917) fails to teach the claimed organic carrier ESL 400.

Maas et al. "Thick-film printing of PZT onto silicon" teaches incorporating an organic binder vehicle of ESL 400 to a powdered PZT to form a PZT paste for thick-film printing (pg. 109).

Therefore it would have been obvious for one skilled in the art at the time the invention was made to have modified GB 2161647 in combination with Buchanan et al. (4,283,228)

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further in combination with Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" still further in combination with Srivastava et al. (5,433,917) by incorporating a organic vehicle of ESL 400 as evidenced by Maas et al. "Thick-film printing of PZT onto silicon" with the expectation of achieving similar success.

Claim 27 is rejected under 35 U.S.C. 103(a) as being unpatentable over GB 2161647 in combination with Buchanan et al. (4,283,228) further in combination with Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" still further in combination with Srivastava et al. (5,433,917) further in combination with Yao et al. "Improved preparation procedure and properties for a multilayer piezoelectric thick-film actuator".

GB 2161647 in combination with Buchanan et al. (4,283,228) further in combination with Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" still further in combination with Srivastava et al. (5,433,917) fails to teach the claimed isostatic pressing step.

Yao et al. "Improved preparation procedure and properties for a multilayer piezoelectric thick-film actuator" teaches incorporating a high isostatic pressure step on a green PZT film before firing and bonding to an electrode (abstract).

Therefore it would have been obvious for one skilled in the art at the time the invention was made to have modified GB 2161647 in combination with Buchanan et al. (4,283,228) further in combination with Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" still further in combination with Srivastava et al. (5,433,917) process by incorporating a high isostatic pressing step as evidenced by Yao et al. "Improved preparation

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procedure and properties for a multilayer piezoelectric thick-film actuator" because of the improved material density and bonding strength resulting from the pressing step.

Claim 32 is rejected under 35 U.S.C. 103(a) as being unpatentable over GB 2161647 in combination with Buchanan et al. (4,283,228) further in combination with Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" still further in combination with Srivastava et al. (5,433,917) further in combination with Chen et al. "Dielectric, ferroelectric and piezoelectric properties of lead zirconate titanate thick films on silicon substrates".

GB 2161647 in combination with Buchanan et al. (4,283,228) further in combination with Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" still further in combination with Srivastava et al. (5,433,917) fails to teach the claimed platinum substrate.

Chen et al. "Dielectric, ferroelectric and piezoelectric properties of lead zirconate titanate thick films on silicon substrates" teaches forming PZT films on platinum buffered silicon substrates (abstract).

Therefore it would have been obvious for one skilled in the art at the time the invention was made to have modified over GB 2161647 in combination with Buchanan et al. (4,283,228) further in combination with Fernandez et al. "Processing and microstructure of porous and dense PZT thick films on Al₂O₃" still further in combination with Srivastava et al. (5,433,917) by utilizing a platinum buffered substrate as evidenced by Chen et al. "Dielectric, ferroelectric and

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piezoelectric properties of lead zirconate titanate thick films on silicon substrates" with the expectation of achieving similar success.

Response to Amendment

6. Applicant's arguments filed 7/29/08 have been fully considered but they are not persuasive.

Applicant argued that the prior art failed to teach the sintering agent being in a liquid phase metal oxide.

Srivastava et al. (5,433,917) teaches this limitation as noted above.

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Brian K. Talbot whose telephone number is (571) 272-1428. The examiner can normally be reached on Monday-Friday 8AM-4PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Timothy H. Meeks can be reached on (571) 272-1423. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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/Brian K Talbot/ Primary Examiner, Art Unit 1792

BKT